

C Claeys

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/10799160/publications.pdf>

Version: 2024-02-01

444
papers

6,195
citations

117453

34
h-index

155451

55
g-index

445
all docs

445
docs citations

445
times ranked

2404
citing authors

#	ARTICLE	IF	CITATIONS
1	Low Frequency Noise: A Show Stopper for State-of-the-art and Future Si, Ge-based and III-V Technologies. , 2021, , .		0
2	Improved physics-based analysis to discriminate the flicker noise origin at very low temperature and drain voltage polarization. Solid-State Electronics, 2020, 171, 107771.	0.8	2
3	Electrical Activity of Extended Defects in Relaxed In _x Ga _{1-x} As Hetero-Epitaxial Layers. ECS Journal of Solid State Science and Technology, 2020, 9, 033001.	0.9	2
4	Are Extended Defects a Show Stopper for Future III-V CMOS Technologies. Journal of Physics: Conference Series, 2019, 1190, 012001.	0.3	1
5	Comparison between proton irradiated triple gate SOI TFETs and finfets from a TID point of view. Semiconductor Science and Technology, 2019, 34, 065003.	1.0	2
6	Low-Frequency Noise Assessment of Work Function Engineering Cap Layers in High-k Gate Stacks. ECS Journal of Solid State Science and Technology, 2019, 8, N25-N31.	0.9	12
7	Advanced CMOS Integration Technologies for Future Mobile Applications. , 2019, , .		1
8	Can we optimize the gate oxide quality of DRAM input/output pMOSFETs by a post-deposition treatment?. Semiconductor Science and Technology, 2019, 34, 015017.	1.0	0
9	Low Frequency Noise Analysis of Impact of Metal Gate Processing on the Gate Oxide Stack Quality. ECS Journal of Solid State Science and Technology, 2018, 7, Q26-Q32.	0.9	8
10	Ground Plane Impact on the Threshold Voltage of Relaxed Ge pFinFETs. , 2018, , .		0
11	Performance of differential pair circuits designed with line tunnel FET devices at different temperatures. Semiconductor Science and Technology, 2018, 33, 075012.	1.0	5
12	Random telegraph signal noise in advanced high performance and memory devices. , 2016, , .		4
13	Split CV mobility at low temperature operation of Ge pFinFETs fabricated with STI first and last processes. Semiconductor Science and Technology, 2016, 31, 114002.	1.0	2
14	Low frequency noise and fin width study of silicon passivated germanium pFinFETs. , 2016, , .		1
15	Effective hole mobility and low-frequency noise characterization of Ge pFinFETs. , 2016, , .		4
16	Analog parameters of solid source Zn diffusion In _x Ga _{1-x} As nTFETs down to 10 K. Semiconductor Science and Technology, 2016, 31, 124001.	1.0	5
17	Low Temperature Effect on Strained and Relaxed Ge pFinFETs STI Last Processes. ECS Transactions, 2016, 75, 213-218.	0.3	3
18	Low-Frequency Noise Assessment of the Oxide Trap Density in Thick-Oxide Input-Output Transistors for DRAM Applications. ECS Journal of Solid State Science and Technology, 2016, 5, N27-N31.	0.9	11

#	ARTICLE	IF	CITATIONS
19	Understanding and optimizing the floating body retention in FDSOI UTBOX. Solid-State Electronics, 2016, 117, 123-129.	0.8	4
20	Random telegraph noise: The key to single defect studies in nano-devices. Thin Solid Films, 2016, 613, 2-5.	0.8	8
21	Review "Device Assessment of Electrically Active Defects in High-Mobility Materials. ECS Journal of Solid State Science and Technology, 2016, 5, P3149-P3165.	0.9	18
22	Performance of TFET and FinFET devices applied to current mirrors for different dimensions and temperatures. Semiconductor Science and Technology, 2016, 31, 055001.	1.0	10
23	Enhanced dynamic threshold voltage UTBB SOI nMOSFETs. Solid-State Electronics, 2015, 112, 19-23.	0.8	10
24	High temperature influence on analog parameters of Bulk and SOI nFinFETs. , 2015, , .		1
25	(Invited) Advanced Semiconductor Devices for Future CMOS Technologies. ECS Transactions, 2015, 66, 49-60.	0.3	3
26	Proton Radiation Effects on the Analog Performance of Bulk n- and p-FinFETs. ECS Transactions, 2015, 66, 295-301.	0.3	3
27	Comparison of Current Mirrors Designed with TFET or FinFET Devices for Different Dimensions and Temperatures. ECS Transactions, 2015, 66, 303-308.	0.3	2
28	Low frequency noise spectroscopy in rotated UTBOX nMOSFETs. , 2015, , .		8
29	Low-frequency noise study of Ge p-MOSFETs with $\text{HfO}_2/\text{Al}_2\text{O}_3/\text{GeO}_x$ gate stack. , 2015, , .		1
30	Detailed analysis of transport properties of FinFETs through Y-Function method: Effects of substrate orientation and strain. , 2015, , .		1
31	Impact of processing and back-gate biasing conditions on the low-frequency noise of ultra-thin buried oxide silicon-on-insulator nMOSFETs. Solid-State Electronics, 2015, 105, 37-44.	0.8	4
32	DC and noise characteristics of underlap Ultra-Thin BOX SOI nMOSFETs. , 2015, , .		0
33	Identification of Si film traps in p-channel SOI FinFETs using low temperature noise spectroscopy. Solid-State Electronics, 2015, 112, 1-6.	0.8	10
34	Static and low frequency noise characterization in standard and rotated UTBOX nMOSFETs. , 2015, , .		3
35	Effect of extension architecture on the LF noise of UTBOX SOI MOSFETs. , 2015, , .		0
36	The smaller the noisier? Low frequency noise diagnostics of advanced semiconductor devices. , 2015, , .		2

#	ARTICLE	IF	CITATIONS
37	Different stress techniques and their efficiency on triple-gate SOI n-MOSFETs. Solid-State Electronics, 2015, 103, 209-215.	0.8	3
38	Impact of Pre- and Post-Growth Treatment on the Low-Frequency Noise of InGaAs nMOSFETs. ECS Transactions, 2014, 60, 115-120.	0.3	2
39	Ground plane influence on enhanced dynamic threshold UTBB SOI nMOSFETs. , 2014, , .		6
40	Low frequency noise characterization of advanced and end of the roadmap devices. , 2014, , .		2
41	Geometry Dependence of Total-Dose Effects in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2014, 61, 2951-2958.	1.2	54
42	Analog performance of standard and uniaxial strained triple-gate SOI FinFETs under x-ray radiation. Semiconductor Science and Technology, 2014, 29, 125015.	1.0	2
43	Study of Random Telegraph Noise in UTBOX Silicon-on-Insulator nMOSFETs. ECS Transactions, 2014, 60, 109-114.	0.3	3
44	Low-Frequency-Noise-Based Oxide Trap Profiling in Replacement High- κ /Metal-Gate pMOSFETs. ECS Journal of Solid State Science and Technology, 2014, 3, Q127-Q131.	0.9	11
45	Performances under saturation operation of p-channel FinFETs on SOI substrates at cryogenic temperature. , 2014, , .		2
46	In depth static and low-frequency noise characterization of n-channel FinFETs on SOI substrates at cryogenic temperature. Solid-State Electronics, 2014, 98, 12-19.	0.8	12
47	Defect assessment and leakage control in Ge junctions. Microelectronic Engineering, 2014, 125, 33-37.	1.1	18
48	Low-frequency noise assessment in advanced UTBOX SOI nMOSFETs with different gate dielectrics. Solid-State Electronics, 2014, 97, 14-22.	0.8	28
49	Improved retention times in UTBOX nMOSFETs for 1T-DRAM applications. Solid-State Electronics, 2014, 97, 30-37.	0.8	8
50	Impact of oxide trap passivation by fluorine on the low-frequency noise behavior of gate-last pMOSFETs. , 2013, , .		4
51	Low frequency noise characterization in n-channel UTBOX devices with 6 nm Si film. , 2013, , .		6
52	Detailed characterisation of SOI n-FinFETs at very low temperature. , 2013, , .		2
53	Analysis of border traps in high- κ gate dielectrics on high-mobility channels. , 2013, , .		0
54	Potential and limitations of UTBB SOI for advanced CMOS technologies. , 2013, , .		5

#	ARTICLE	IF	CITATIONS
55	Study of the impact of doping concentration and Schottky barrier height on ohmic contacts to n-type germanium. <i>Microelectronic Engineering</i> , 2013, 106, 129-131.	1.1	8
56	Drain currents and their excess noise in triple gate bulk p-channel FinFETs of different geometry. <i>Microelectronics Reliability</i> , 2013, 53, 394-399.	0.9	0
57	NW-TFET analog performance for different Ge source compositions. , 2013, , .		11
58	Comparative Experimental Study between Tensile and Compressive Uniaxially Stressed nMuGFETs under X-ray Radiation Focusing on Analog Behavior. <i>ECS Transactions</i> , 2013, 53, 177-185.	0.3	0
59	Semiconductor Film Bandgap Influence on Retention Time of UTBOX SOI 1T-FBRAM. <i>ECS Transactions</i> , 2013, 53, 139-146.	0.3	2
60	Low-Frequency Noise in High-K and SiO ₂ UTBOX SOI nMOSFETs. <i>ECS Transactions</i> , 2013, 52, 87-92.	0.3	1
61	The Generation Rate Analysis of Different S/D Junction Engineering in Scaled UTBOX 1T-DRAM. <i>ECS Transactions</i> , 2013, 53, 195-201.	0.3	2
62	(Invited) Status and Trends in Ge CMOS Technology. <i>ECS Transactions</i> , 2013, 54, 25-37.	0.3	19
63	Lessons Learned from Low-Frequency Noise Studies on Fully Depleted UTBOX Silicon-On-Insulator nMOSFETs. <i>ECS Transactions</i> , 2013, 53, 49-61.	0.3	6
64	Low-Frequency-Noise-Based Oxide Trap Profiling in Replacement High-k/Metal-Gate pMOSFETs. <i>ECS Transactions</i> , 2013, 58, 281-292.	0.3	3
65	Low-Frequency Noise Studies on Fully Depleted UTBOX Silicon-on-Insulator nMOSFETs: Challenges and Opportunities. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, Q205-Q210.	0.9	14
66	Influence of X-ray radiation on standard and uniaxial strained triple-gate SOI FinFETs. , 2013, , .		2
67	Impact of Disturb on Retention Time in Single FBRAM Cells. <i>ECS Meeting Abstracts</i> , 2013, , .	0.0	1
68	On the Variability of the Low-Frequency Noise in UTBOX SOI nMOSFETs. <i>ECS Transactions</i> , 2012, 49, 51-58.	0.3	3
69	Uniaxial and/or Biaxial Strain Influence on MuGFET Devices. <i>Journal of the Electrochemical Society</i> , 2012, 159, H570-H574.	1.3	0
70	Spacer Length and Tilt Implantation Influence on Scaled UTBOX FD MOSFETs. <i>ECS Transactions</i> , 2012, 49, 483-489.	0.3	1
71	Biaxial + uniaxial stress effectiveness in tri-gate SOI nMOSFETs with variable fin dimensions. , 2012, , .		1
72	Origin of wide retention distribution in 1T Floating Body RAM. , 2012, , .		7

#	ARTICLE	IF	CITATIONS
73	Uniaxial mechanical stress influence on the low frequency noise in FD SOI nMOSFETs operating in saturation. , 2012, , .		0
74	Gate length impact on UTBOX FBRAM devices. , 2012, , .		2
75	Challenges and opportunities in advanced Ge pMOSFETs. Materials Science in Semiconductor Processing, 2012, 15, 588-600.	1.9	72
76	Low-Frequency Noise Assessment of the Oxide Quality of Gate-Last High- k pMOSFETs. IEEE Electron Device Letters, 2012, 33, 1366-1368.	2.2	8
77	High-energy neutrons effect on strained and non-strained SOI MuGFETs and planar MOSFETs. Microelectronics Reliability, 2012, 52, 118-123.	0.9	2
78	Low frequency noise characterization in n-channel FinFETs. Solid-State Electronics, 2012, 70, 20-26.	0.8	27
79	GIDL behavior of p- and n-MuGFET devices with different TiN metal gate thickness and high-k gate dielectrics. Solid-State Electronics, 2012, 70, 44-49.	0.8	6
80	Radiation damage of Si $_{1-x}$ Ge $_x$ S/D p-type metal oxide semiconductor field effect transistor with different Ge concentrations. Thin Solid Films, 2012, 520, 3337-3340.	0.8	9
81	Laser- and Heavy Ion-Induced Charge Collection in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2011, 58, 2563-2569.	1.2	58
82	Ge content and recess depth dependence of the band-to-band tunneling current in Si $_{1-x}$ Ge $_x$ /Ge $_x$ /Si hetero-junctions. , 2011, , .		0
83	Assessment of temperature dependence of the low frequency noise in unstrained and strained FinFETs. , 2011, , .		3
84	Low-frequency noise in triple-gate n-channel bulk FinFETs. , 2011, , .		7
85	Impact of proton irradiation on strained triple gate SOI p- and n-MOSFETs. , 2011, , .		3
86	Study of ohmic contacts to n-type Ge: Snowplow and laser activation. Applied Physics Letters, 2011, 99, .	1.5	32
87	Investigation of Tri-Gate FinFETs by Noise Methods. Engineering Materials, 2011, , 287-306.	0.3	1
88	Defect-Related Excess Low-Frequency Noise in Ge-on-Si pMOSFETs. IEEE Electron Device Letters, 2011, 32, 87-89.	2.2	10
89	Pulsed laser-induced transient currents in bulk and silicon-on-insulator FinFETs. , 2011, , .		12
90	Low-Frequency Noise Characterization of Strained Germanium pMOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 3132-3139.	1.6	19

#	ARTICLE	IF	CITATIONS
91	Influence of the sidewall crystal orientation, HfSiO nitridation and TiN metal gate thickness on n-MuGFETs under analog operation. <i>Solid-State Electronics</i> , 2011, 62, 146-151.	0.8	4
92	Evaluation of electron irradiated embedded SiGe source/drain diodes by Raman spectroscopy. <i>Microelectronic Engineering</i> , 2011, 88, 484-487.	1.1	3
93	Gate-edge charges related effects and performance degradation in advanced multiple-gate MOSFETs. <i>Solid-State Electronics</i> , 2011, 59, 18-24.	0.8	11
94	LKE and BGI Lorentzian noise in strained and non-strained tri-gate SOI FinFETs with HfSiON/SiO ₂ gate dielectric. <i>Solid-State Electronics</i> , 2011, 63, 27-36.	0.8	0
95	Uniaxial stress efficiency for different fin dimensions of triple-gate SOI nMOSFETs. , 2011, , .		2
96	Analysis of the Temperature Dependence of Trap-Assisted Tunneling in Ge pFET Junctions. <i>Journal of the Electrochemical Society</i> , 2011, 158, H955.	1.3	17
97	High Doping Density/High Electric Field, Stress and Heterojunction Effects on the Characteristics of CMOS Compatible p-n Junctions. <i>Journal of the Electrochemical Society</i> , 2011, 158, R27.	1.3	21
98	SOI MOSFET Transconductance Behavior from Micro to Nano Era. <i>Engineering Materials</i> , 2011, , 267-286.	0.3	0
99	Degradation of GaN LEDs by electron irradiation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010, 173, 57-60.	1.7	15
100	Si versus Ge for future microelectronics. <i>Thin Solid Films</i> , 2010, 518, 2301-2306.	0.8	19
101	P+/n junction leakage in thin selectively grown Ge-in-STI substrates. <i>Thin Solid Films</i> , 2010, 518, 2489-2492.	0.8	11
102	Low-frequency noise assessment of the silicon passivation of Ge pMOSFETs. <i>Thin Solid Films</i> , 2010, 518, 2493-2496.	0.8	14
103	Short-channel epitaxial germanium pMOS transistors. <i>Thin Solid Films</i> , 2010, 518, S88-S91.	0.8	5
104	Effects of electron irradiation on SiGe devices. <i>Thin Solid Films</i> , 2010, 518, 2517-2520.	0.8	4
105	Device performance of p-Ge MOSFETs at liquid nitrogen temperature. <i>Thin Solid Films</i> , 2010, 518, 2513-2516.	0.8	0
106	Effect of rotation, gate-dielectric and SEG on the noise behavior of advanced SOI MuGFETs. <i>Solid-State Electronics</i> , 2010, 54, 178-184.	0.8	12
107	Low-frequency noise and static analysis of the impact of the TiN metal gate thicknesses on n- and p-channel MuGFETs. <i>Solid-State Electronics</i> , 2010, 54, 1592-1597.	0.8	10
108	Modeling impact of electric field and strain on the leakage of embedded SiGe source/drain junctions. , 2010, , .		1

#	ARTICLE	IF	CITATIONS
109	Zero-Temperature-Coefficient of planar and MuGFET SOI devices. , 2010, , .		7
110	Fin shape influence on the analog performance of standard and strained MuGFETs. , 2010, , .		8
111	Influence of Fin Width on the Total Dose Behavior of p-Channel Bulk MuGFETs. IEEE Electron Device Letters, 2010, 31, 243-245.	2.2	26
112	Extended-Defect Aspects of Ge-on-Si Materials and Devices. Journal of the Electrochemical Society, 2010, 157, R1.	1.3	12
113	Electrical-Based ESD Characterization of Ultrathin-Body SOI MOSFETs. IEEE Transactions on Device and Materials Reliability, 2010, 10, 130-141.	1.5	7
114	DIBL performance of 60 MeV proton-irradiated SOI MuGFETs. , 2010, , .		2
115	Analytical model for the $1/f$ noise in the tunneling current through metal-oxide-semiconductor structures. Journal of Applied Physics, 2009, 106, .	1.1	25
116	On the frequency dispersion of the capacitance-voltage behavior of epitaxial Ge on Si p+n junctions. Journal of Applied Physics, 2009, 106, 074511.	1.1	9
117	Electric field dependence of trap-assisted-tunneling current in strained SiGe source/drain junctions. Applied Physics Letters, 2009, 94, 233507.	1.5	7
118	Low-frequency Noise Analysis of the Impact of an LaO Cap Layer in HfSiON/Ta ₂ C Gate Stack nMOSFETs. ECS Transactions, 2009, 25, 237-245.	0.3	10
119	What Do We Know about Hydrogen-Induced Thermal Donors in Silicon?. Journal of the Electrochemical Society, 2009, 156, H434.	1.3	25
120	Low-Frequency Noise Behavior in P-channel SOI FinFETs Processed With Different Strain Techniques. , 2009, , .		3
121	On the $1/f$ noise of triple-gate field-effect transistors with high- k gate dielectric. Applied Physics Letters, 2009, 95, 032101.	1.5	16
122	Impact of the TiN Layer Thickness on the Low-Frequency Noise and Static Device Performance of n-Channel MuGFETs. , 2009, , .		0
123	Low-Frequency Noise of Strained and Non-Strained n-Channel Tri-Gate FinFETs With Different Gate Dielectrics. , 2009, , .		1
124	Linear kink effect Lorentzians in the noise spectra of n- and p-channel fin field-effect transistors processed in standard and strained silicon-on-insulator substrates. Solid-State Electronics, 2009, 53, 613-620.	0.8	2
125	Physics of fluctuation processes in downscaled silicon MOSFETs. Radiophysics and Quantum Electronics, 2009, 52, 655-670.	0.1	1
126	Strained Si/SiGe MOS technology: Improving gate dielectric integrity. Microelectronic Engineering, 2009, 86, 218-223.	1.1	24

#	ARTICLE	IF	CITATIONS
127	1/f noise study on strained Si _{0.8} Ge _{0.2} p-channel MOSFETs with high-k/poly Si gate stack. Solid-State Electronics, 2009, 53, 1177-1182.	0.8	0
128	Cryogenic operation of FinFETs aiming at analog applications. Cryogenics, 2009, 49, 590-594.	0.9	21
129	1/f Noise in Drain and Gate Current of MOSFETs With High-k Gate Stacks. IEEE Transactions on Device and Materials Reliability, 2009, 9, 180-189.	1.5	107
130	Reliability performance characterization of SOI FinFETs. , 2009, , .		1
131	Impact of TiN metal gate thickness and the HfSiO nitridation on MuGFETs electrical performance. , 2009, , .		0
132	On the Temperature and Field Dependence of Trap-Assisted Tunneling Current in Ge p^+n Junctions. IEEE Electron Device Letters, 2009, 30, 562-564.	2.2	49
133	High gate voltage drain current leveling off and its low-frequency noise in 65nm fully-depleted strained and non-strained SOI nMOSFETs. Solid-State Electronics, 2008, 52, 801-807.	0.8	6
134	Impact of strain and source/drain engineering on the low frequency noise behaviour in n-channel tri-gate FinFETs. Solid-State Electronics, 2008, 52, 1889-1894.	0.8	21
135	Carrier lifetime analysis in thin gate oxide FD-SOI n-MOSFETs by gate-induced drain current transients. Journal of Materials Science: Materials in Electronics, 2008, 19, 161-165.	1.1	0
136	Degradation of SiC-MESFETs by irradiation. Journal of Materials Science: Materials in Electronics, 2008, 19, 175-178.	1.1	0
137	Effects of electron and proton irradiation on embedded SiGe source/drain diodes. Materials Science in Semiconductor Processing, 2008, 11, 310-313.	1.9	4
138	Impact strain engineering on gate stack quality and reliability. Solid-State Electronics, 2008, 52, 1115-1126.	0.8	69
139	Defect engineering aspects of advanced Ge process modules. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 49-55.	1.7	14
140	Radiation damage in proton-irradiated strained Si n-MOSFETs. Materials Science in Semiconductor Processing, 2008, 11, 314-318.	1.9	4
141	Stress analysis of Si _{1-x} Ge _x embedded source/drain junctions. Materials Science in Semiconductor Processing, 2008, 11, 285-290.	1.9	7
142	Influence of the pre-treatment anneal on Co germanide Schottky contacts. Materials Science in Semiconductor Processing, 2008, 11, 300-304.	1.9	6
143	Impact of Donor Concentration, Electric Field, and Temperature Effects on the Leakage Current in Germanium p^+n Junctions. IEEE Transactions on Electron Devices, 2008, 55, 2287-2296.	1.6	69
144	Paramagnetic point defects at interfacial layers in biaxial tensile strained (100)Si/SiO ₂ . Journal of Applied Physics, 2008, 103, .	1.1	17

#	ARTICLE	IF	CITATIONS
145	Processing Factors Impacting the Leakage Current and Flicker Noise of Germanium p ⁺ -n Junctions on Silicon Substrates. Journal of the Electrochemical Society, 2008, 155, H145.	1.3	9
146	Improved generation lifetime model for the electrical characterization of single- and double-gate SOI nMOSFETs. Semiconductor Science and Technology, 2008, 23, 125011.	1.0	5
147	Study of metal-related deep-level defects in germanide Schottky barriers on n-type germanium. Journal of Applied Physics, 2008, 104, .	1.1	22
148	Low temperature noise spectroscopy of 0.1 μ m partially depleted silicon on insulator metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2007, 101, 104511.	1.1	45
149	Behavior of the 1/f noise and electron mobility in 65 nm FD SOI nMOSFETs employing different tensile-strain-inducing techniques. AIP Conference Proceedings, 2007, .	0.3	3
150	The Low-Frequency Noise Behavior of pMOSFETs with Embedded SiGe Source/Drain Regions. AIP Conference Proceedings, 2007, .	0.3	1
151	The Length-Dependence of the 1/f Noise of Graded-Channel SOI nMOSFETs. ECS Transactions, 2007, 9, 373-381.	0.3	1
152	On the Low-Frequency Noise of pMOSFETs With Embedded SiGe Source/Drain and Fully Silicided Metal Gate. IEEE Electron Device Letters, 2007, 28, 987-989.	2.2	19
153	On the origin of the 1 \cdot f noise in shallow germanium p+n junctions. Applied Physics Letters, 2007, 90, 043501.	1.5	6
154	Leakage Current Control in Recessed SiGe Source/Drain Junctions. Journal of the Electrochemical Society, 2007, 154, H814.	1.3	12
155	Low Temperature Operation of Undoped Body Triple-Gate FinFETs from an Analog Perspective. ECS Transactions, 2007, 9, 19-27.	0.3	1
156	Analysis of the Pre-epi Bake Conditions on the Defect Creation in Recessed SiGe S/D Junctions. ECS Transactions, 2007, 11, 47-53.	0.3	3
157	Low-Frequency Noise Assessment of Silicon Passivated Ge pMOSFETs With TiN/TaN/ HfO_2 Gate Stack. IEEE Electron Device Letters, 2007, 28, 288-291.	2.2	35
158	Analysis of junction leakage in advanced germanium P+/n junctions. , 2007, .		8
159	Geometry and Strain Dependence of the Proton Radiation Behavior of MuGFET Devices. IEEE Transactions on Nuclear Science, 2007, 54, 2227-2232.	1.2	29
160	On the Origin of the Excess Low-Frequency Noise in Graded-Channel Silicon-on-Insulator nMOSFETs. IEEE Electron Device Letters, 2007, 28, 919-921.	2.2	4
161	Low-frequency noise in silicon-on-insulator devices and technologies. Solid-State Electronics, 2007, 51, 16-37.	0.8	94
162	The low-frequency noise behaviour of graded-channel SOI nMOSFETs. Solid-State Electronics, 2007, 51, 260-267.	0.8	12

#	ARTICLE	IF	CITATIONS
163	Evaluation of triple-gate FinFETs with SiO ₂ /HfO ₂ /TiN gate stack under analog operation. Solid-State Electronics, 2007, 51, 285-291.	0.8	32
164	Impact of the gate-electrode/dielectric interface on the low-frequency noise of thin gate oxide n-channel metal-oxide-semiconductor field-effect transistors. Solid-State Electronics, 2007, 51, 627-632.	0.8	13
165	Gate induced floating body effects in TiN/SiON and TiN/HfO ₂ gate stack triple gate SOI nFinFETs. Solid-State Electronics, 2007, 51, 1201-1210.	0.8	5
166	Temperature impact on the Lorentzian noise induced by electron valence-band tunneling in partially depleted SOI p-MOSFETs. Solid-State Electronics, 2007, 51, 1180-1184.	0.8	2
167	Dose rate dependence of radiation-induced lattice defects and performance degradation in npn Si bipolar transistors by 2-MeV electron irradiation. Physica B: Condensed Matter, 2007, 401-402, 469-472.	1.3	4
168	Electrical stress on irradiated thin gate oxide partially depleted SOI nMOSFETs. Microelectronic Engineering, 2007, 84, 2081-2084.	1.1	8
169	Dose rate dependence of the back gate degradation in thin gate oxide PD-SOI MOSFETs by 2-MeV electron irradiation. Microelectronic Engineering, 2007, 84, 2125-2128.	1.1	5
170	Performance degradation mechanism of irradiated GaAlAs LED. Physica B: Condensed Matter, 2007, 401-402, 33-36.	1.3	0
171	Effect of gate interface on performance degradation of irradiated SiC-MESFET. Physica B: Condensed Matter, 2007, 401-402, 37-40.	1.3	2
172	A DLTS study on plasma-hydrogenated n-type high-resistivity magnetic Cz silicon. Journal of Materials Science: Materials in Electronics, 2007, 18, 705-710.	1.1	6
173	Lifetime and leakage current considerations in metal-doped germanium. Journal of Materials Science: Materials in Electronics, 2007, 18, 799-804.	1.1	16
174	Interfacial layer quality effects on low-frequency noise (1/f) in p-MOSFETs with advanced gate stacks. Microelectronics Reliability, 2007, 47, 501-504.	0.9	4
175	Low-frequency (1/f) noise behavior of locally stressed HfO ₂ /TiN gate-stack pMOSFETs. IEEE Electron Device Letters, 2006, 27, 508-510.	2.2	27
176	Impact of the interfacial layer on the low-frequency noise (1/f) behavior of MOSFETs with advanced gate stacks. IEEE Electron Device Letters, 2006, 27, 688-691.	2.2	54
177	Effect of Nitridation on Low-Frequency (1/f) Noise in n- and p-MOSFETS with HfO ₂ Gate Dielectrics. Journal of the Electrochemical Society, 2006, 153, G819.	1.3	12
178	Radiation-induced defects in SiC-MESFETs after 2-MeV electron irradiation. Physica B: Condensed Matter, 2006, 376-377, 382-384.	1.3	16
179	1/f noise performance of MOSFETs with HfO ₂ and metal gate on Ge-on-insulator substrates. Materials Science in Semiconductor Processing, 2006, 9, 721-726.	1.9	18
180	Radiation damage in electron-irradiated strained Si n-MOSFETs. Materials Science in Semiconductor Processing, 2006, 9, 732-736.	1.9	1

#	ARTICLE	IF	CITATIONS
181	A deep-level transient spectroscopy study of Co- and Ni-germanided n-type germanium. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 554-558.	1.9	12
182	The temperature mobility degradation influence on the zero temperature coefficient of partially and fully depleted SOI MOSFETs. <i>Microelectronics Journal</i> , 2006, 37, 952-957.	1.1	20
183	Gate electrode effects on low-frequency (1/f) noise in p-MOSFETs with high- ϵ^p dielectrics. <i>Solid-State Electronics</i> , 2006, 50, 992-998.	0.8	27
184	Investigation of back gate interface states by drain current hysteresis in PD-SOI n-MOSFETs. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 416-419.	1.3	8
185	Radiation source dependence of device performance degradation for 4H-SiC MESFETs. <i>Superlattices and Microstructures</i> , 2006, 40, 632-637.	1.4	0
186	Electron valence-band tunnelling excess noise in twin-gate silicon-on-insulator MOSFETs. <i>Solid-State Electronics</i> , 2006, 50, 52-57.	0.8	8
187	Hot-carrier-induced degradation of drain current hysteresis and transients in thin gate oxide floating body partially depleted SOI nMOSFETs. <i>Microelectronics Reliability</i> , 2006, 46, 1657-1663.	0.9	3
188	Impact on the back gate degradation in partially depleted SOI n-MOSFETs by 2-MeV electron irradiation. <i>Microelectronics Reliability</i> , 2006, 46, 1731-1735.	0.9	3
189	Thermal donor formation in direct-plasma hydrogenated n-type Czochralski silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2006, 134, 189-192.	1.7	8
190	Processing aspects in the low-frequency noise of nMOSFETs on strained-silicon substrates. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 1039-1047.	1.6	35
191	Gate Bias Effect on the 60-MeV Proton Irradiation Response of 65-nm CMOS nMOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 1815-1820.	1.6	2
192	Low-Frequency ($1/f$) Noise Performance of n- and p-MOSFETs with Poly-Si \cdot Hf-Based Gate Dielectrics. <i>Journal of the Electrochemical Society</i> , 2006, 153, G324.	1.3	21
193	Analysis of the Leakage Current Origin in Thin Strain Relaxed Buffer Substrates. <i>Journal of the Electrochemical Society</i> , 2006, 153, G379.	1.3	15
194	Estimating Temperature Dependence of Generation Lifetime Extracted from Drain Current Transients. <i>Journal of the Electrochemical Society</i> , 2006, 153, G502.	1.3	7
195	1/f Noise as a Tool to Assess Fermi Level Pinning (EF) at the HfO ₂ /poly-Si Interface in High-k n-MOSFETs. <i>ECS Transactions</i> , 2006, 2, 503-513.	0.3	1
196	Defect Engineering Considerations for Strained Silicon Substrates. <i>ECS Transactions</i> , 2006, 2, 349-361.	0.3	3
197	Analysis of 2-MeV Electron-Irradiation Induced Degradation in FD-SOI MOSFETs Fabricated on ELTRAN and UNIBOND Wafers. <i>IEEE Transactions on Nuclear Science</i> , 2006, 53, 1939-1944.	1.2	2
198	Bias Dependence of Gate Oxide Degradation of 90 nm CMOS Transistors Under 60 MeV Proton Irradiation. <i>IEEE Transactions on Nuclear Science</i> , 2006, 53, 1959-1966.	1.2	4

#	ARTICLE	IF	CITATIONS
199	Deep level transient spectroscopy study of nickel-germanide Schottky barriers on n-type germanium. Applied Physics Letters, 2006, 88, 183506.	1.5	21
200	Inherent density of point defects in thermal tensile strained (100)Si ⁺ •SiO ₂ entities probed by electron spin resonance. Applied Physics Letters, 2006, 89, 152103.	1.5	16
201	Hydrogen-plasma-induced thermal donors in high resistivity n-type magnetic Czochralski-grown silicon. Applied Physics Letters, 2006, 89, 031911.	1.5	10
202	Impact of strain-engineering on the low-frequency noise performance of advanced MOSFETs. , 2006, , .		5
203	Impact of high-k gate stack material with metal gates on LF noise in n- and p-MOSFETs. Microelectronic Engineering, 2005, 80, 226-229.	1.1	36
204	Radiation source dependence of performance degradation in thin gate oxide fully-depleted SOI n-MOSFETs. Microelectronics Reliability, 2005, 45, 1376-1381.	0.9	0
205	Tunneling $1/f^3$ noise in 5nm HfO ₂ /2.1nm SiO ₂ gate stack n-MOSFETs. Solid-State Electronics, 2005, 49, 702-707.	0.8	33
206	Impact of hot-carrier stress on gate-induced floating body effects and drain current transients of thin gate oxide partially depleted SOI nMOSFETs. Solid-State Electronics, 2005, 49, 1536-1546.	0.8	8
207	Impact of Direct Plasma Hydrogenation on Thermal Donor Formation in n-Type CZ Silicon. Journal of the Electrochemical Society, 2005, 152, G16.	1.3	15
208	Low-Frequency Noise Characterization of 90 nm Multiple Gate Oxide CMOS Transistors. AIP Conference Proceedings, 2005, , .	0.3	0
209	P-N Junction Diodes Fabricated Based on Donor Formation in Plasma Hydrogenated P-Type Czochralski Silicon. Materials Research Society Symposia Proceedings, 2005, 864, 9261.	0.1	0
210	Low-Frequency Noise Performance of HfO ₂ -Based Gate Stacks. Journal of the Electrochemical Society, 2005, 152, F115.	1.3	36
211	Impact of Gate Material on Low-frequency Noise of nMOSFETs with 1.5 nm SiON Gate Dielectric: Testing the Limits of the Number Fluctuations Theory. AIP Conference Proceedings, 2005, , .	0.3	6
212	Defect analysis of strained silicon on thin strain-relaxed buffer layers for high mobility transistors. Journal of Physics Condensed Matter, 2005, 17, S2197-S2210.	0.7	12
213	Electrically active defects in irradiated n-type Czochralski silicon doped with group IV impurities. Journal of Physics Condensed Matter, 2005, 17, S2255-S2266.	0.7	16
214	Origin of the front-back-gate coupling in partially depleted and fully depleted silicon-on-insulator metal-oxide-semiconductor field-effect transistors with accumulated back gate. Journal of Applied Physics, 2005, 98, 114506.	1.1	20
215	The lower boundary of the hydrogen concentration required for enhancing oxygen diffusion and thermal donor formation in Czochralski silicon. Journal of Applied Physics, 2005, 98, 033511.	1.1	7
216	On the beneficial impact of tensile-strained silicon substrates on the low-frequency noise of n-channel metal-oxide-semiconductor transistors. Applied Physics Letters, 2005, 86, 223509.	1.5	20

#	ARTICLE	IF	CITATIONS
217	Bias dependence of gate oxide degradation of 90 nm CMOS transistors under 60 MeV proton irradiation. European Conference on Radiation and Its Effects on Components and Systems, Proceedings of the, 2005, , .	0.0	1
218	Linear-kink-noise suppression in partially depleted SOI using the twin-gate MOSFET configuration. IEEE Electron Device Letters, 2005, 26, 510-512.	2.2	7
219	Electrical stresses on ultra-thin gate oxide SOI MOSFETs after irradiation. IEEE Transactions on Nuclear Science, 2005, 52, 2252-2258.	1.2	14
220	Effect of high-temperature electron irradiation in thin gate oxide FD-SOI n-MOSFETs. IEEE Transactions on Nuclear Science, 2005, 52, 2392-2397.	1.2	1
221	Back-Gate Induced Noise Overshoot in Partially-Depleted SOI MOSFETs. NATO Science Series Series II, Mathematics, Physics and Chemistry, 2005, , 255-260.	0.1	2
222	High-energy proton irradiation induced changes in the linear-kink noise overshoot of 0.10 μm partially depleted silicon-on-insulator metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2004, 95, 4084-4092.	1.1	11
223	Correlation between the $1/f$ noise parameters and the effective low-field mobility in HfO ₂ gate dielectric n-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2004, 85, 1057-1059.	1.5	39
224	Local Electric Fields in Silicided Shallow Junctions. Journal of the Electrochemical Society, 2004, 151, G578.	1.3	1
225	A study on radiation damage of IGBTs by 2-MeV electrons at different irradiation temperatures. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 676-679.	0.6	7
226	Low-frequency noise behavior of SiO ₂ /HfO ₂ dual-layer gate dielectric nMOSFETs with different interfacial oxide thickness. IEEE Transactions on Electron Devices, 2004, 51, 780-784.	1.6	136
227	Critical Discussion of the Front-Back Gate Coupling Effect on the Low-Frequency Noise in Fully Depleted SOI MOSFETs. IEEE Transactions on Electron Devices, 2004, 51, 1008-1016.	1.6	36
228	Excess Lorentzian Noise in Partially Depleted SOI nMOSFETs Induced by an Accumulation Back-Gate Bias. IEEE Electron Device Letters, 2004, 25, 433-435.	2.2	14
229	DLTS Studies of high-temperature electron irradiated Cz n-Si. Physica Status Solidi A, 2004, 201, 509-516.	1.7	8
230	Short-channel effects in the Lorentzian noise induced by the EVB tunneling in partially-depleted SOI MOSFETs. Solid-State Electronics, 2004, 48, 747-758.	0.8	16
231	Total ionizing dose damage in deep submicron partially depleted SOI MOSFETs induced by proton irradiation. Solid-State Electronics, 2004, 48, 1045-1054.	0.8	24
232	Impact of gate tunneling floating-body charging on drain current transients of 0.10 μm -CMOS partially depleted SOI MOSFETs. Solid-State Electronics, 2004, 48, 1211-1221.	0.8	12
233	Impact of 7.5-MeV proton irradiation on front-back gate coupling effect in ultra thin gate oxide FD-SOI n-MOSFETs. IEEE Transactions on Nuclear Science, 2004, 51, 3795-3800.	1.2	21
234	Anomalous threshold voltage change by 2 MeV electron irradiation at 100 $^{\circ}\text{C}$ in deep submicron metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2004, 84, 3088-3090.	1.5	1

#	ARTICLE	IF	CITATIONS
235	Characterization of Oxide Precipitates in Heavily B-Doped Silicon by Infrared Spectroscopy. Journal of the Electrochemical Society, 2004, 151, G598.	1.3	8
236	Low-Frequency Noise Assessment for Deep Submicrometer CMOS Technology Nodes. Journal of the Electrochemical Society, 2004, 151, G307.	1.3	32
237	Electron irradiation effect on thermal donors in CZ-Si. EPJ Applied Physics, 2004, 27, 133-135.	0.3	2
238	Physics and Modeling of Radiation Effects in Advanced CMOS Technology Nodes. , 2004, , 181-190.		1
239	Noise and Tunneling Through the 2.5 nm Gate Oxide in Soi MOSFETs. , 2004, , 129-136.		0
240	Electron valence-band tunneling-induced Lorentzian noise in deep submicron silicon-on-insulator metalâ€“oxideâ€“semiconductor field-effect transistors. Journal of Applied Physics, 2003, 94, 4461-4469.	1.1	37
241	"Linear kink effect" induced by electron valence band tunneling in ultrathin gate oxide bulk and SOI MOSFETs. IEEE Transactions on Electron Devices, 2003, 50, 1675-1682.	1.6	113
242	Gated-diode study of corner and peripheral leakage current in high-energy neutron irradiated silicon p-n junctions. IEEE Transactions on Nuclear Science, 2003, 50, 278-287.	1.2	6
243	Impact of the high vertical electric field on low-frequency noise in thin-gate oxide MOSFETs. IEEE Transactions on Electron Devices, 2003, 50, 2520-2527.	1.6	14
244	Induced lattice defects in InGaAs photodiodes by high-temperature electron irradiation. Physica B: Condensed Matter, 2003, 340-342, 337-340.	1.3	9
245	Comparison of electron irradiation effect on thermal donors in Cz and oxygen doped FZ silicon. Physica B: Condensed Matter, 2003, 340-342, 1022-1025.	1.3	3
246	A novel approach to analyse FTIR spectra of precipitates in boron-doped silicon. Physica B: Condensed Matter, 2003, 340-342, 1013-1017.	1.3	6
247	Extraction of the carrier generation and recombination lifetime from the forward characteristics of advanced diodes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 189-192.	1.7	13
248	Characterisation of oxygen and oxygen-related defects in highly- and lowly-doped silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 207-212.	1.7	9
249	Model for the radiation degradation of polycrystalline silicon films. IEEE Transactions on Nuclear Science, 2003, 50, 2481-2485.	1.2	0
250	Deep Levels in Oxygenated n-Type High-Resistivity FZ Silicon before and after a Low-Temperature Hydrogenation Step. Journal of the Electrochemical Society, 2003, 150, G520.	1.3	5
251	Explaining the parameters of the electron valence-band tunneling related Lorentzian noise in fully depleted SOI MOSFETs. IEEE Electron Device Letters, 2003, 24, 751-754.	2.2	17
252	Activation energy analysis as a tool for extraction and investigation of pâ€“n junction leakage current components. Journal of Applied Physics, 2003, 94, 1218-1221.	1.1	39

#	ARTICLE	IF	CITATIONS
253	Damage coefficient in high-temperature particle- and $\hat{1}^3$ -irradiated silicon p-n diodes. Applied Physics Letters, 2003, 82, 296-298.	1.5	8
254	Short-channel radiation effect in 60 MeV proton irradiated 0.13 $\hat{1}^4$ m CMOS transistors. IEEE Transactions on Nuclear Science, 2003, 50, 2426-2432.	1.2	61
255	Diode Analysis of Advanced Processing Modules for Deep-Submicrometer CMOS Technology Nodes. Journal of the Electrochemical Society, 2003, 150, G795.	1.3	4
256	Low-frequency noise overshoot in ultrathin gate oxide silicon-on-insulator metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2003, 82, 1790-1792.	1.5	34
257	Recovery behaviour resulting from thermal annealing in n-MOSFETs irradiated by 20 MeV protons. Semiconductor Science and Technology, 2003, 18, 506-511.	1.0	7
258	Hydrogen plasma-enhanced thermal donor formation in n-type oxygen-doped high-resistivity float-zone silicon. Applied Physics Letters, 2002, 81, 1842-1844.	1.5	22
259	Oxide phase determination in silicon using infrared spectroscopy and transmission electron microscopy techniques. Journal of Applied Physics, 2002, 91, 2493-2498.	1.1	28
260	Improved extraction of carrier concentration and depletion width from capacitance-voltage characteristics of silicon n+p-well junction diodes. Applied Physics Letters, 2002, 80, 1192-1194.	1.5	12
261	On the Origin of the 1/f. , 2002, , .		1
262	Substrate orientation, doping and plasma frequency dependencies of structural defect formation in hydrogen plasma treated silicon. Journal of Physics Condensed Matter, 2002, 14, 13037-13045.	0.7	27
263	Optical spectroscopy of oxygen precipitates in heavily doped p-type silicon. Journal of Physics Condensed Matter, 2002, 14, 13185-13193.	0.7	2
264	The 1/f ^{sup 1.7} noise in submicron SOI MOSFETs with 2.5 nm nitrided gate oxide. IEEE Transactions on Electron Devices, 2002, 49, 2367-2370.	1.6	19
265	Impact of fast-neutron irradiation on the silicon p-n junction leakage and role of the diffusion reverse current. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 166-170.	0.6	3
266	$\hat{1}^3$ -irradiation hardness of short-channel nMOSFETs fabricated in a SOI technology. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 429-434.	0.6	4
267	Hydrogen enhanced thermal donor formation in oxygen enriched high resistive float-zone silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 116-120.	0.6	4
268	Radiation damage in flash memory cells. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 392-400.	0.6	6
269	Radiation effects on the current-voltage and capacitance-voltage characteristics of advanced p-n junction diodes surrounded by shallow trench isolation. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 409-413.	0.6	2
270	DLTS and PL studies of proton radiation defects in tin-doped FZ silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 19-23.	0.6	13

#	ARTICLE	IF	CITATIONS
271	Radiation damage of polycrystalline silicon films. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 176-180.	0.6	6
272	Random Telegraph Signal: a local probe for single point defect studies in solid-state devices. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 136-143.	1.7	59
273	Extraction of the oxide charge density at front and back interfaces of SOI nMOSFETs devices. Solid-State Electronics, 2002, 46, 1381-1387.	0.8	2
274	Parasitic conduction in a 0.13 μ m CMOS technology at low temperature. European Physical Journal Special Topics, 2002, 12, 61-64.	0.2	4
275	Radiation Effects and Low-Frequency Noise in Silicon Technologies. , 2001, , 385-510.		0
276	Excess carrier cross-sectional profiling technique for determination of the surface recombination velocity. Materials Science in Semiconductor Processing, 2001, 4, 125-131.	1.9	27
277	Statistical analysis of shallow p ⁺ n junction leakage increase using XTEM results probabilities. Materials Science in Semiconductor Processing, 2001, 4, 105-107.	1.9	4
278	Lifetime study in advanced isolation techniques. Materials Science in Semiconductor Processing, 2001, 4, 137-139.	1.9	3
279	High-energy proton radiation induced defects in tin-doped n-type silicon. Physica B: Condensed Matter, 2001, 308-310, 477-480.	1.3	6
280	Induced lattice defects in InGaAsP laser diodes by high-temperature gamma ray irradiation. Physica B: Condensed Matter, 2001, 308-310, 1185-1188.	1.3	6
281	Electrical characterization of shallow cobalt-silicided junctions. Journal of Materials Science: Materials in Electronics, 2001, 12, 207-210.	1.1	2
282	Degradation and recovery of AlGaAs/GaAs p-HEMT irradiated by high-energy particle. Microelectronics Reliability, 2001, 41, 79-85.	0.9	10
283	Radiation damages of polycrystalline silicon films and npn Si transistors by high-energy particle irradiation. Microelectronics Reliability, 2001, 41, 1443-1448.	0.9	4
284	Impact of CMOS processing steps on the drain current kink of NMOSFETs at liquid helium temperature. IEEE Transactions on Electron Devices, 2001, 48, 1207-1215.	1.6	12
285	Impact of a high electric field on the extraction of the generation lifetime from the reverse generation current component of shallow n ⁺ /p-well diodes. IEEE Transactions on Electron Devices, 2001, 48, 2445-2446.	1.6	13
286	Silicon Devices and Circuits. , 2001, , 105-257.		6
287	Radiation damage of InGaAsP laser diodes by high-temperature gamma-ray and electron irradiation. , 2001, , .		1
288	Diode Analysis of High-Energy Boron Implantation-Induced P-Well Defects. Journal of the Electrochemical Society, 2001, 148, G507.	1.3	5

#	ARTICLE	IF	CITATIONS
289	Carbon Enhancement of SiO ₂ Nucleation in Buried Oxide Synthesis—Computer Simulations and Secondary Ion Mass Spectroscopy Depth Profiling. <i>Journal of the Electrochemical Society</i> , 2001, 148, F92.	1.3	3
290	Improved extraction of the activation energy of the leakage current in silicon n-junction diodes. <i>Applied Physics Letters</i> , 2001, 78, 1997-1999.	1.5	15
291	Tin Doping of Silicon for Controlling Oxygen Precipitation and Radiation Hardness. <i>Journal of the Electrochemical Society</i> , 2001, 148, G738.	1.3	30
292	Hole-trapping-related transients in shallow n+p junctions fabricated in a high-energy boron-implanted p well. <i>Applied Physics Letters</i> , 2001, 78, 949-951.	1.5	11
293	Reliability Aspects of Cryogenic Silicon Technologies. , 2001, , 259-383.		0
294	Flicker noise in deep submicron nMOS transistors. <i>Solid-State Electronics</i> , 2000, 44, 1239-1245.	0.8	13
295	Simultaneous extraction of the silicon film and front oxide thicknesses on fully depleted SOI nMOSFETs. <i>Solid-State Electronics</i> , 2000, 44, 1961-1969.	0.8	4
296	Extraction of the lightly doped drain concentration of fully depleted SOI NMOSFETs using the back gate bias effect. <i>Solid-State Electronics</i> , 2000, 44, 677-684.	0.8	5
297	Impact of neutron irradiation on optical performance of InGaAsP laser diodes. <i>Thin Solid Films</i> , 2000, 364, 259-263.	0.8	11
298	Impact of advanced processing modules on the low-frequency noise performance of deep-submicron CMOS technologies. <i>Microelectronics Reliability</i> , 2000, 40, 1815-1821.	0.9	5
299	Perpendicular excitation-probe microwave absorption technique for carrier lifetime analysis in layered Si structures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 73, 1-6.	1.7	5
300	Silicon substrate effects on the current-voltage characteristics of advanced n-junction diodes. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 73, 191-196.	1.7	11
301	The impact of high-energy proton irradiation on the low-frequency 1/f noise in FZ-silicon diodes. <i>Materials Science in Semiconductor Processing</i> , 2000, 3, 263-267.	1.9	0
302	Impact of the divacancy (?) on the generation-recombination properties of 10 MeV proton irradiated Float-Zone silicon diodes. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2000, 439, 310-318.	0.7	14
303	Influence of the substrate voltage on the random telegraph signal parameters in submicron n-channel metal-oxide-semiconductor field-effect transistors under a constant inversion charge density. <i>Applied Physics A: Materials Science and Processing</i> , 2000, 70, 345-353.	1.1	29
304	Deep levels in high-energy proton-irradiated tin-doped n-type Czochralski silicon. <i>Applied Physics Letters</i> , 2000, 76, 2838-2840.	1.5	22
305	Peripheral current analysis of silicon n-junction and gated diodes. <i>Journal of Applied Physics</i> , 2000, 88, 6506-6514.	1.1	14
306	Impact of cobalt silicidation on the low-frequency noise behavior of shallow p-n junctions. <i>IEEE Electron Device Letters</i> , 2000, 21, 408-410.	2.2	11

#	ARTICLE	IF	CITATIONS
307	Influence of Tin Impurities on the Generation and Annealing of Thermal Oxygen Donors in Czochralski Silicon at 450Å°C. Journal of the Electrochemical Society, 2000, 147, 2727.	1.3	16
308	Impact of 20-MeV $\hat{\pm}$ -ray irradiation on the V-band performance of AlGaAs pseudomorphic HEMTs. IEEE Transactions on Nuclear Science, 2000, 47, 2546-2550.	1.2	11
309	Perspectives of Silicon-on-Insulator Technologies for Cryogenic Electronics. , 2000, , 233-247.		11
310	Reliability aspects of the low-frequency noise behaviour of submicron CMOS technologies. Semiconductor Science and Technology, 1999, 14, R61-R71.	1.0	21
311	Current transients in almost-ideal Czochralski silicon p-n junction diodes. Applied Physics Letters, 1999, 75, 3342-3344.	1.5	2
312	Electrical Quality Assessment of Epitaxial Wafers Based on p-n Junction Diagnostics. Journal of the Electrochemical Society, 1999, 146, 3429-3434.	1.3	9
313	On the flicker noise in submicron silicon MOSFETs. Solid-State Electronics, 1999, 43, 865-882.	0.8	303
314	Radiation-induced lattice defects in InGaAsP laser diodes and their effects on device performance. Physica B: Condensed Matter, 1999, 273-274, 1031-1033.	1.3	4
315	Impact of induced lattice defects on performance degradation of AlGaAs/GaAs p-HEMTs. Physica B: Condensed Matter, 1999, 273-274, 1034-1036.	1.3	5
316	Non-trivial GR and 1/fnoise generated in the p-Si layer of SOI and SOS MOSFETs near the inverted front or buried p-Si/SiO ₂ interface. Semiconductor Science and Technology, 1999, 14, 775-783.	1.0	22
317	Factors determining the lifetime damage coefficients and the low-frequency noise in MeV proton irradiated silicon diodes. Journal of Radioanalytical and Nuclear Chemistry, 1999, 239, 207-211.	0.7	2
318	On the impact of the capture rates on the generation/recombination lifetime ratio of a single deep level. IEEE Transactions on Electron Devices, 1999, 46, 1487-1488.	1.6	20
319	p-n Junction Diagnostics to Determine Surface and Bulk Generation/Recombination Properties of Silicon Substrates. Journal of the Electrochemical Society, 1999, 146, 1151-1157.	1.3	14
320	A low-frequency noise study of hot-carrier stressing effects in submicron Si p-MOSFETs. Microelectronics Reliability, 1998, 38, 23-27.	0.9	6
321	Bulk defect induced low-frequency noise in n/sup +/-p silicon diodes. IEEE Transactions on Electron Devices, 1998, 45, 2528-2536.	1.6	20
322	Factors determining the damage coefficients and the low-frequency noise in MeV proton-irradiated silicon diodes. IEEE Transactions on Nuclear Science, 1998, 45, 89-97.	1.2	9
323	RTS noise due to lateral isolation related defects in submicron nMOSFETs. Microelectronics Reliability, 1998, 38, 1561-1568.	0.9	6
324	A global description of the base current 1/f noise of polysilicon emitter bipolar transistors before and after hot-carrier stress. Solid-State Electronics, 1998, 42, 1679-1687.	0.8	10

#	ARTICLE	IF	CITATIONS
325	Impact of the free electron distribution on the random telegraph signal capture kinetics in submicron n-metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 1998, 73, 2444-2446.	1.5	14
326	Optimized Diode Analysis of Electrical Silicon Substrate Properties. Journal of the Electrochemical Society, 1998, 145, 2107-2112.	1.3	33
327	Processes in Ultrathin Buried Oxide Synthesis Stimulated by Low Dose Ion Implantation. Journal of the Electrochemical Society, 1998, 145, 2964-2969.	1.3	6
328	p-n junction peripheral current analysis using gated diode measurements. Applied Physics Letters, 1998, 72, 3503-3505.	1.5	15
329	Impact of high energy particles on InGaP/InGaAs pseudomorphic HEMTs. IEEE Transactions on Nuclear Science, 1998, 45, 2861-2866.	1.2	21
330	Accurate extraction of the diffusion current in silicon p-n junction diodes. Applied Physics Letters, 1998, 72, 1054-1056.	1.5	26
331	Noise as a Diagnostic Tool for Semiconductor Material and Device Characterization. Journal of the Electrochemical Society, 1998, 145, 2058-2067.	1.3	32
332	Identification of isolation-edge related random telegraph signals in submicron silicon metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 1997, 71, 3874-3876.	1.5	5
333	Degradation and Recovery of Si Diodes by 20-Mev Protons And 220-Mev Carbon Particles. Materials Research Society Symposia Proceedings, 1997, 487, 435.	0.1	1
334	Radiation Damage Of InGaAs Photodiodes By High Energy Particles. Materials Research Society Symposia Proceedings, 1997, 487, 471.	0.1	4
335	Empirical model for the low-frequency noise of hot-carrier degraded submicron LDD MOSFETs. IEEE Electron Device Letters, 1997, 18, 480-482.	2.2	16
336	Hot-carrier stress effects on the amplitude of Random Telegraph Signals in small area Si p-MOSFETS. Microelectronics Reliability, 1997, 37, 1015-1019.	0.9	5
337	Impact of the series resistance on the parameter extraction of submicron silicon metal-oxide-semiconductor transistors operated at 77 K. Solid-State Electronics, 1997, 41, 659-661.	0.8	9
338	Electrical and Structural Properties of Oxygen-Precipitation Induced Extended Defects in Silicon. Journal De Physique III, 1997, 7, 1469-1486.	0.3	13
339	Effective generation-recombination parameters in high-energy proton irradiated silicon diodes. Applied Physics Letters, 1996, 69, 2858-2860.	1.5	33
340	Gate length effect on the RTS noise amplitude in SOI MOSFETs. IEEE Electron Device Letters, 1996, 17, 181-183.	2.2	1
341	Impact of the substrate quality on the low frequency noise of silicon diodes. AIP Conference Proceedings, 1996, , .	0.3	1
342	Process- and irradiation-induced defects in silicon devices. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1996, 377, 244-257.	0.7	2

#	ARTICLE	IF	CITATIONS
343	Back and front interface related generation-recombination noise in buried-channel SOI pMOSFETs. IEEE Transactions on Electron Devices, 1996, 43, 417-423.	1.6	24
344	On the relationship between the bulk recombination lifetime and the excess noise in silicon p-n junction diodes. Solid State Communications, 1996, 98, 961-963.	0.9	3
345	The low-frequency noise behaviour of silicon-on-insulator technologies. Solid-State Electronics, 1996, 39, 949-960.	0.8	97
346	Impact of the starting interstitial oxygen concentration on the electrical characteristics of electron irradiated Si junction diodes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 36, 179-182.	1.7	3
347	The low-frequency noise behaviour of Si n+p junction diodes fabricated on (1 0 0) and (1 1 1) substrates. Physica B: Condensed Matter, 1996, 228, 219-225.	1.3	6
348	Influence of the substrate on the degradation of irradiated Si diodes. Physica Status Solidi A, 1996, 156, 215-223.	1.7	3
349	Impact of Fe and Cu Contamination on the Minority Carrier Lifetime of Silicon Substrates. Journal of the Electrochemical Society, 1996, 143, 3014-3019.	1.3	48
350	Parameter Extraction of MOSFETs Operated at Low Temperature. European Physical Journal Special Topics, 1996, 06, C3-29-C3-42.	0.2	9
351	High energy particle irradiation effects on the low-frequency noise of Czochralski silicon junction diodes. Applied Physics Letters, 1996, 68, 788-790.	1.5	6
352	The response of Si p - n junction diodes to proton irradiation. Semiconductor Science and Technology, 1996, 11, 1434-1442.	1.0	12
353	Impact of the starting interstitial oxygen concentration on the electrical characteristics of electron irradiated Si junction diodes. , 1996, , 179-182.		0
354	On the Recombination Activity of Oxygen Precipitation Related Lattice Defects in Silicon. Materials Research Society Symposia Proceedings, 1995, 378, 35.	0.1	5
355	The cryogenic operation of partially depleted silicon-on-insulator inverters. IEEE Transactions on Electron Devices, 1995, 42, 1100-1105.	1.6	14
356	Correlation between the low-frequency noise spectral density and the static device parameters of silicon-on-insulator MOSFETs. IEEE Transactions on Electron Devices, 1995, 42, 1467-1472.	1.6	10
357	Substrate current characteristics in partially depleted silicon-on-insulator n-MOSFETs from room temperature down to 4.2 K. Cryogenics, 1995, 35, 321-326.	0.9	3
358	Static characteristics of gate-all-around SOI MOSFETs at cryogenic temperatures. Physica Status Solidi A, 1995, 148, 635-642.	1.7	3
359	In-situ HVEM study of dislocation generation in patterned stress fields at silicon surfaces. Physica Status Solidi A, 1995, 150, 497-506.	1.7	5
360	A new method for determining the front and back interface trap densities of accumulation mode SOI MOSFETs at 77K. Solid-State Electronics, 1995, 38, 1799-1803.	0.8	7

#	ARTICLE	IF	CITATIONS
361	D.c. and low frequency noise characteristics of ^{13}C -irradiated gate-all-around silicon-on-insulator MOS transistors. Solid-State Electronics, 1995, 38, 1-8.	0.8	73
362	Impact of silicidation on the excess noise behaviour of mos transistors. Solid-State Electronics, 1995, 38, 1893-1897.	0.8	46
363	Low-frequency noise characterisation of ^{13}C -irradiated silicon-on-insulator MOSFETs. Nuclear Instruments & Methods in Physics Research B, 1995, 95, 75-81.	0.6	2
364	Substrate bias effect on the capture kinetics of random telegraph signals in submicron $\text{p}^+\text{-channel}$ silicon metal-oxide-semiconductor transistors. Applied Physics Letters, 1995, 66, 598-600.	1.5	9
365	Impact of oxygen related extended defects on silicon diode characteristics. Journal of Applied Physics, 1995, 77, 5669-5676.	1.1	74
366	Extraction of the minority carrier recombination lifetime from forward diode characteristics. Applied Physics Letters, 1995, 66, 2894-2896.	1.5	41
367	Substrate bias effect on the random telegraph signal parameters in submicrometer silicon $\text{p}^+\text{-metal-oxide-semiconductor}$ transistors. Journal of Applied Physics, 1995, 77, 910-914.	1.1	13
368	Impact of the substrate on the low-frequency noise of silicon n+p junction diodes. Applied Physics Letters, 1995, 66, 2507-2509.	1.5	32
369	Low-frequency noise behaviour of high-energy electron irradiated Si n+p junction diodes. Electronics Letters, 1995, 31, 1016-1018.	0.5	8
370	Static and low-frequency noise characteristics of n+p junction diodes fabricated in different silicon substrates. Semiconductor Science and Technology, 1995, 10, 1002-1008.	1.0	17
371	Sensitive Light Scattering as a Semiquantitative Method for Studying Photoresist Stripping. Journal of the Electrochemical Society, 1995, 142, 211-216.	1.3	26
372	The Perspectives of Silicon-on-Insulator Technologies for Cryogenic Applications. Journal of the Electrochemical Society, 1994, 141, 2522-2532.	1.3	22
373	The cryogenic behaviour of metal-oxide-semiconductor transistors fabricated in high-resistivity silicon substrates. Semiconductor Science and Technology, 1994, 9, 1679-1685.	1.0	4
374	Impact of twin-gate concept on silicon-on-insulator inverters. Electronics Letters, 1994, 30, 454-456.	0.5	7
375	Deep levels in heat-treated and ^{252}Cf -irradiated p-type silicon substrates with different oxygen content. Semiconductor Science and Technology, 1994, 9, 1474-1479.	1.0	8
376	Empirical relationship between the low-frequency noise spectral density and the transconductance of silicon-on-insulator $\text{p}^+\text{-channel}$ metal-oxide-semiconductor transistors. Applied Physics Letters, 1994, 65, 1946-1948.	1.5	10
377	Random telegraph signals in silicon-on-insulator metal-oxide-semiconductor transistors. Journal of Applied Physics, 1994, 75, 3647-3653.	1.1	14
378	On the gate- and drain-voltage dependence of the RTS amplitude in submicron MOSTs. Applied Physics A: Solids and Surfaces, 1994, 58, 353-358.	1.4	22

#	ARTICLE	IF	CITATIONS
379	Development of silicon micropattern pixel detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1994, 348, 399-408.	0.7	25
380	The use of body ties in partially depleted SOI MOSTs operating at cryogenic temperatures. Solid-State Electronics, 1994, 37, 1933-1936.	0.8	6
381	The low-frequency noise overshoot in partially depleted n-channel silicon-on-insulator twin-MOST's. IEEE Transactions on Electron Devices, 1994, 41, 1972-1976.	1.6	12
382	Transient effects in accumulation mode p-channel SOI MOSFET's operating at 77 K. IEEE Transactions on Electron Devices, 1994, 41, 519-523.	1.6	7
383	Generation and annealing behaviour of MeV proton and ²⁵² Cf irradiation induced deep levels in silicon diodes. IEEE Transactions on Nuclear Science, 1994, 41, 479-486.	1.2	19
384	On the impact of low fluence irradiation with MeV particles on silicon diode characteristics and related material properties. IEEE Transactions on Nuclear Science, 1994, 41, 1924-1931.	1.2	22
385	Combined low-frequency noise and random telegraph signal analysis of silicon MOSFET's. Applied Surface Science, 1993, 63, 285-290.	3.1	13
386	Alternative random telegraph signal mechanisms in silicon-on-insulator MOS transistors. Microelectronic Engineering, 1993, 22, 185-188.	1.1	4
387	The low-frequency noise behaviour at room temperature and at 77 K of pMOSTs fabricated on high-resistivity silicon substrates. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1993, 327, 523-528.	0.7	1
388	Gate-length dependence of the low-frequency noise overshoot in partially depleted SOI n-MOSFET's. Solid State Communications, 1993, 88, 507-508.	0.9	1
389	Simple method for the determination of the interface trap density at 77 K in fully depleted accumulation mode SOI MOSFETs. Solid-State Electronics, 1993, 36, 827-832.	0.8	7
390	Back-gate induced random telegraph signal noise in fully-depleted silicon-on-insulator nMOSFETs. Solid-State Electronics, 1993, 36, 1593-1596.	0.8	4
391	A consistent experimental method for the extraction of the threshold voltage of SOI nMOSFETs from room down to cryogenic temperatures. Solid-State Electronics, 1993, 36, 1465-1468.	0.8	4
392	Hot-carrier degradation of nMOSTs stressed at 4.2 K. Solid-State Electronics, 1993, 36, 527-532.	0.8	3
393	Recent progress in the understanding of crystallographic defects in silicon. Journal of Crystal Growth, 1993, 126, 41-62.	0.7	16
394	Hot-Carrier degradation of the Random Telegraph Signal amplitude in submicrometer Si MOSTs. Applied Physics A: Solids and Surfaces, 1993, 57, 283-289.	1.4	25
395	Evidence of different conduction mechanisms in accumulation-mode p-channel SOI MOSFET's at room and liquid-helium temperatures. IEEE Transactions on Electron Devices, 1993, 40, 727-732.	1.6	24
396	A low-frequency noise study of gate-all-around SOI transistors. IEEE Transactions on Electron Devices, 1993, 40, 2054-2059.	1.6	21

#	ARTICLE	IF	CITATIONS
397	The hysteresis and transient behavior of Si metal-oxide-semiconductor transistors at 4.2 K. II. Prekink clockwise hysteresis regime. Journal of Applied Physics, 1993, 73, 3074-3081.	1.1	8
398	The hysteresis and transient behavior of Si metal-oxide-semiconductor transistors at 4.2 K. I. The kink-related counterclockwise hysteresis regime. Journal of Applied Physics, 1993, 73, 3068-3073.	1.1	18
399	Integration of CMOS-electronics and particle detector diodes in high-resistivity silicon-on-insulator wafers. IEEE Transactions on Nuclear Science, 1993, 40, 753-758.	1.2	25
400	Metastable charge-trapping effect in SOI nMOSTs at 4.2 K. Semiconductor Science and Technology, 1993, 8, 423-428.	1.0	7
401	Low-frequency noise behavior of ^{13}C -irradiated partially depleted silicon-on-insulator channel metal-oxide-semiconductor transistors. Applied Physics Letters, 1993, 63, 1672-1674.	1.5	8
402	Evidence for an alternative, hole-trapping related random telegraph signal mechanism in channel silicon-on-insulator metal-oxide-semiconductor transistors. Applied Physics Letters, 1993, 62, 876-878.	1.5	8
403	Liquid-helium temperature hot-carrier degradation of Si p-channel MOSTs. IEE Proceedings, Part G: Circuits, Devices and Systems, 1993, 140, 431.	0.2	2
404	Combined low-frequency noise and random telegraph signal analysis of silicon MOSFET's. , 1993, , 285-290.		0
405	Study of electrically active lattice defects in Cf-252 and proton irradiated silicon diodes. IEEE Transactions on Nuclear Science, 1992, 39, 1747-1753.	1.2	15
406	Substrate current characteristics of Si N- and PMOST's at 4.2 K. Solid State Communications, 1992, 82, 341-343.	0.9	9
407	Random telegraph signal noise: A probe for hot-carrier degradation effects in submicrometer MOSFET's?. Microelectronic Engineering, 1992, 19, 605-608.	1.1	6
408	Low temperature behaviour of submicron accumulation mode p-channel SOI MOSFETs. Microelectronic Engineering, 1992, 19, 857-860.	1.1	4
409	Kink-related noise overshoot in SOI n-MOSFETS operating at 4.2 K. Electronics Letters, 1992, 28, 577.	0.5	14
410	A study of the kink-related excess low-frequency noise in silicon-on-insulator metal-oxide-semiconductor transistors operated at liquid helium temperatures. Journal of Applied Physics, 1992, 72, 1416-1422.	1.1	11
411	Deep-level transient spectroscopy of detector-grade high-resistivity float-zone silicon. Journal of Electronic Materials, 1992, 21, 533-541.	1.0	5
412	Short-channel pMOSTs in a high-resistivity silicon substrate. I. Analytical model. IEEE Transactions on Electron Devices, 1992, 39, 2268-2277.	1.6	10
413	Short-channel pMOSTs in a high-resistivity silicon substrate. II. Noise performance. IEEE Transactions on Electron Devices, 1992, 39, 2278-2283.	1.6	4
414	Influence of hot-carrier stress on the kink/hysteresis behaviour of NMOST's operating at liquid temperatures. Microelectronic Engineering, 1991, 15, 457-460.	1.1	7

#	ARTICLE	IF	CITATIONS
415	Investigation of drain current RTS noise in small area silicon MOS transistors. Microelectronic Engineering, 1991, 15, 547-550.	1.1	11
416	Design implications of a p-well CMOS technology for the realization of monolithic integrated pixel arrays. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1991, 305, 541-548.	0.7	9
417	Anomalous kink-related excess noise in MOSFETs at 4.2 K. IEEE Transactions on Electron Devices, 1991, 38, 907-912.	1.6	20
418	The importance of the internal bulk-source potential on the low temperature kink in NMOSTs. IEEE Transactions on Electron Devices, 1991, 38, 1459-1466.	1.6	21
419	Transient response of silicon devices at 4.2 K. II. Application to the case of a metal-oxide-semiconductor transistor. Semiconductor Science and Technology, 1991, 6, 905-911.	1.0	17
420	The behavior of silicon p-n junction based devices at liquid helium temperatures. Journal of Applied Physics, 1991, 70, 1016-1024.	1.1	40
421	Analytical model for the current-voltage characteristics of a silicon resistor at liquid helium temperatures. Cryogenics, 1990, 30, 1152-1159.	0.9	11
422	Analytical model for the kink in nMOSTs operating at Liquid Helium Temperatures (LHT). Solid-State Electronics, 1990, 33, 445-454.	0.8	27
423	The charge transport in a silicon resistor at liquid helium temperatures. Journal of Applied Physics, 1990, 68, 4091-4099.	1.1	32
424	Freeze-out effects on NMOS transistor characteristics at 4.2 K. IEEE Transactions on Electron Devices, 1989, 36, 1155-1161.	1.6	45
425	Two- and three-dimensional calculation of substrate resistance. IEEE Transactions on Electron Devices, 1988, 35, 339-352.	1.6	21
426	Design impact on drain multiplication latch-up triggering. Microelectronics Journal, 1988, 19, 39-48.	1.1	0
427	New concepts for integrated solid state detector electronics. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1988, 273, 625-629.	0.7	16
428	The influence of the drain multiplication current on latchup behavior. IEEE Transactions on Electron Devices, 1988, 35, 1810-1819.	1.6	9
429	Gettering mechanisms in silicon. Journal of Applied Physics, 1988, 64, 869-876.	1.1	85
430	Model for hysteresis and kink behavior of MOS transistors operating at 4.2 K. IEEE Transactions on Electron Devices, 1988, 35, 1120-1125.	1.6	70
431	Film edge induced dislocation generation in silicon substrates. III. High voltage transmission electron microscopy observations and theoretical results for (11,11) and (011) silicon substrates. Journal of Applied Physics, 1988, 63, 5703-5711.	1.1	16
432	A Quantitative Model for Silicon Yield Stress Calculations at Thin Film Edges. Journal of the Electrochemical Society, 1988, 135, 1509-1517.	1.3	20

#	ARTICLE	IF	CITATIONS
433	Film-induced dislocation generation in silicon substrates. I. Theoretical model. Journal of Applied Physics, 1987, 61, 2170-2175.	1.1	72
434	A theoretical study of the critical radius of precipitates and its application to silicon oxide in silicon. Journal of Applied Physics, 1987, 62, 3960-3967.	1.1	127
435	Film-induced dislocation generation in silicon substrates. II. Application of the theoretical model for local oxidation processes on (001) silicon substrates. Journal of Applied Physics, 1987, 61, 2176-2188.	1.1	46
436	A two-dimensional model for the kink in nMOSTs operating at liquid helium temperatures. , 0, , .		5
437	Integration of CMOS-electronics in an SOI layer on high-resistivity silicon substrates. , 0, , .		2
438	Detector diodes and test devices fabricated in high resistivity SOI wafers. , 0, , .		1
439	Low-frequency noise and DC characterization of ionization damage in a 1- μ m SOI CMOS technology adapted for space applications. , 0, , .		1
440	A unified approach for hot-carrier degradation of current gain and 1/f noise of polysilicon emitter bipolar transistors. , 0, , .		2
441	Comparison of the total-dose and 60 MeV proton-irradiation response of CMOS transistors operated at 4.2 K. , 0, , .		2
442	60 MeV proton irradiation effects on NO-annealed and standard-oxide deep submicron MOSFETs. , 0, , .		5
443	Electron valence band tunnelling induced excess Lorentzian noise in fully depleted SOI transistors. , 0, , .		4
444	Defect Engineering and Stress Control in Advanced Devices on High-Mobility Substrates. , 0, , .		0